

**DXTN07100BP5** 

### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	I <sub>CM</sub>	6	A

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit		
	(Note 5)		3.2			
Power Dissipation	(Note 6)	$P_{D}$	1.7	W		
	(Note 7)		0.74	1		
	(Note 5)		39			
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{ heta JA}$	75	20.004		
	(Note 7)		169	°C/W		
Thermal Resistance, Junction to Leads	(Note 8)	R <sub>θJL</sub>	9			
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

#### ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

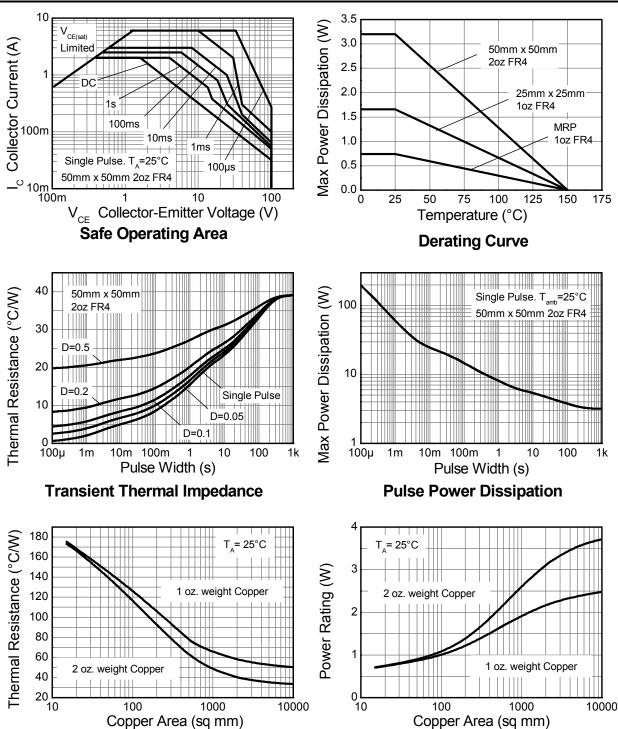
Notes:

- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.
  7. Same as note (5), except mounted on minimum recommended pad (MRP) layout.
  9. Thormal resistance from invertion to ender spirit (on the exposed collector and).

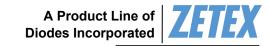
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad). 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristics and Derating Information**







DXTN07100BP5

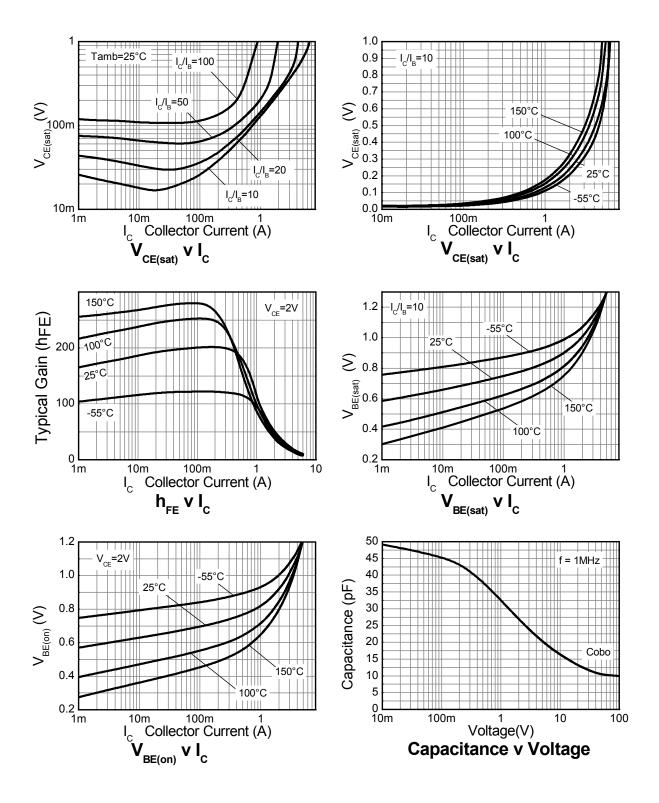
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	120	_	_	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	100	_	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	_	_	>	I <sub>E</sub> = 100μA
Collector Cutoff Current	I <sub>CBO</sub>	_		0.1 10	μΑ	V <sub>CB</sub> = 100V V <sub>CB</sub> = 100V, T <sub>AMB</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	0.1	μA	V <sub>EB</sub> = 4V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	_	0.13 0.23	0.3 0.5	>	$I_C = 1A$ , $I_B = 100mA$ $I_C = 2A$ , $I_B = 200mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	_	0.9	1.25	>	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	_	0.8	1.00	V	I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V
DC Current Gain (Note 10)	h <sub>FE</sub>	70 100 55 25	200 200 110 55	300 — —	I	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 2V I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2V I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V I <sub>C</sub> = 2A, V <sub>CE</sub> = 2V
Transition Frequency	f <sub>T</sub>	140	175	_	MHz	$I_C = 100 \text{mA}, \ V_{CE} = 5 \text{V}$ f = 100MHz
Output Capacitance	C <sub>obo</sub>	_	_	30	pF	V <sub>CB</sub> = 10A, f = 1MHz
Switching Times	t <sub>on</sub> t <sub>off</sub>	_	80 1200	_	ns ns	I <sub>C</sub> = 500mA, V <sub>CC</sub> = 10V, I <sub>B1</sub> = I <sub>B2</sub> = 50mA

Note: 10. Pulse Test: Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2.0%.



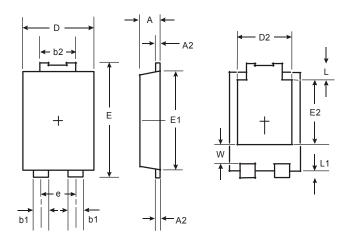
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





# **Package Outline Dimensions**

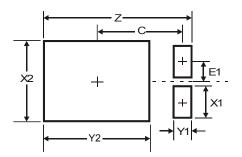
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



PowerDI <sup>®</sup> 5				
Dim	Min	Max		
Α	1.05	1.15		
A2	0.33	0.43		
b1	0.80	0.99		
b2	1.70	1.88		
D	3.90	4.05		
D2	3.054 Typ			
E	6.40	6.60		
е	1.84	Тур		
E1	5.30 5.45			
E2	3.549 Typ			
L	0.75	0.95		
L1	0.50	0.65		
W	1.10	1.41		
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)			
Z	6.6			
X1	1.4			
X2	3.6			
Y1	0.8			
Y2	4.7			
С	3.87			
E1	0.9			

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





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